

Nano- and Micro-Scale simulations of Ge/3C-SiC and Ge/4H-SiC NN-heterojunction diodes

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Nano and micro-scale simulations of Si/4H-SiC and Si/3C-SiC NN-heterojunction diodes

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Nanoscale and microscale simulations of N-N junction heterostructures of 3C-4H silicon carbide

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Simulations of heterostructures based on 3C-4H and 6H-4H silicon carbide polytypes

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